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### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
	AA AB					

### FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Translation (Yes or No)
AH AK			

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### OTHER DOCUMENTS

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<i>TN</i>		NIKKEI MICRODEVICES, February 1994, pages 92 to 93. Discussed at Page 2 of the Specification.
<i>TN</i>		OYO BUTURI, Volume 68, No. 7, 1999, pages 793-796.
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<i>TN</i>	P	Nakamura et al., "Present Status of InGaN/GaN/AlGaIn based laser diodes", Proceedings of the Second International Conference on Nitride Semiconductors - ICNS '97 - pp.444-446.
Examiner	<i>T. NGUYEN</i>	
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